# NSN 5961-00-003-4779

Thyristor Semiconductor Device - Page 1 of 1

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**Inclosure Material:**

Metal

**Overall Length:**

1.204 inches

**Mounting Facility Quantity:**

1

**Mounting Method:**

Threaded stud

**Features Provided:**

Hermetically sealed case

**Overall Width Across Flats:**

Between 0.424 inches and 0.437 inches

**Thread Size:**

0.190 inches

**Semiconductor Material:**

Silicon

**Voltage Rating In Volts Per Characteristic:**

50.0 breakover voltage, dc

**Current Rating Per Characteristic:**

60.00 amperes forward current, average absolute

**Power Rating Per Characteristic:**

500.0 milliwatts peak gate power dissipation

**Maximum Operating Tempurature Per Measurement Point:**

150.0 degrees celsius case

**Test Data Document:**

98230-0n149987 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

**Thread Series Designator:**

Unf

**Terminal Type And Quantity:**

2 tab, solder lug and 1 threaded stud

**Shelf Life:**

N/a

**Unit Of Measure:**

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**Demilitarization:**

No

**Fiig:**

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